

Epi - Wafer

Undoped GaN



Feature Undoped GaN Epi. Wafer
Single side polished (Growth surface)

Diameter 2" (50.8mm)

**Thickness
(Included substrate)** 430 μ m $\pm$ 15 μ m

Structure u-GaN / Sapphire substrate



GaN on Sapphire Wafer

Characteristics (at 25°C)

Parameter		Typ.	Test Conditions
PL measurement	Peak wavelength	362nm $\pm$ 2nm	Etamax PLATO Laser : 266nm
	Uniformity STD	<3%	
	FWHM	<10nm	
	FWHM STD	<3%	
Thickness	Thickness	$\sim$ 2 μ m (+/-10% std)	
	Thickness STD	<10%	
XRD	(002)	<350 arcsec	Panalytical HRXRD
	(102)	<450 arcsec	
Hall	Carrier Concentration	< -1×10^{17} /cm ³	Accent HL5500
	Mobility	>200 cm ² /V-sec	
Doping material	Si	N/A	-
	Mg	N/A	

Normalized Single Spectrum(300 ~ 700nm)

